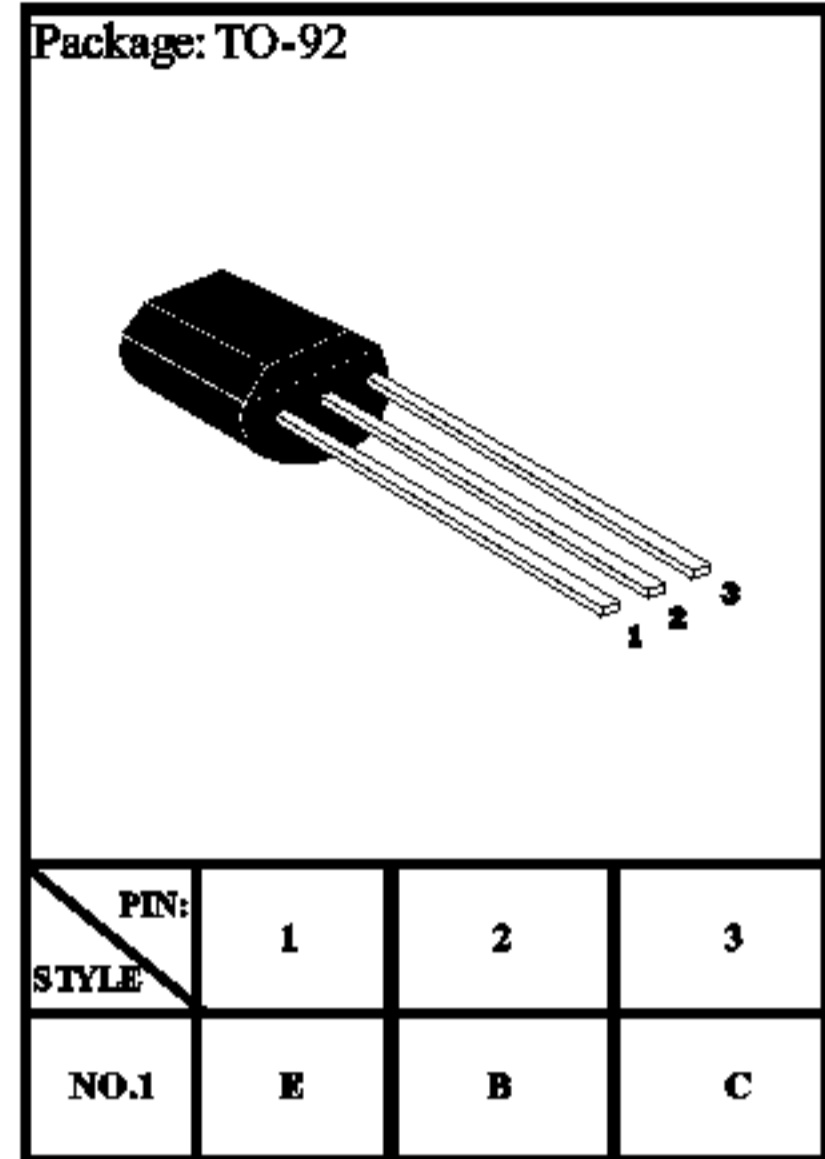




GENERAL PURPOSE TRANSISTOR

- * Complement to 2N3906
- * Collector-Emitter Voltage $V_{CEO}=40V$
- * Collector Dissipation: $P_c=625\text{ mW}$ ($T_a=25^\circ C$)



ABSOLUTE MAXIMUM RATINGS at $T_{amb}=25^\circ C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	60	V
Collector-Emitter Voltage	V_{ceo}	40	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	200	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

ELECTRICAL CHARACTERISTICS at $T_{amb}=25^\circ C$

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{cbo}	60			V	$I_c=10\mu A$ $I_e=0$
Collector-Emitter Breakdown Voltage	BV_{ceo}	40			V	$I_c=1\text{ mA}$ $I_b=0$
Emitter-Base Breakdown Voltage	BV_{ebo}	6			V	$I_e=10\mu A$ $I_c=0$
Collector Cutoff Current	I_{cex}			50	nA	$V_{ce}=30V$ $V_{eb}=3V$
Emitter Cutoff Current	I_{ebo}			50	nA	$V_{eb}=3V$ $I_c=0$
DC Current Gain	H_{fe1}	40				$V_{ce}=1v$ $I_c=0.1\text{ mA}$
DC Current Gain	H_{fe2}	70				$V_{ce}=1v$ $I_c=1\text{ mA}$
DC Current Gain	H_{fe3}	100		300		$V_{ce}=1v$ $I_c=10\text{ mA}$
DC Current Gain	H_{fe4}	60				$V_{ce}=1v$ $I_c=50\text{ mA}$
DC Current Gain	H_{fe5}	30				$V_{ce}=1v$ $I_c=100\text{ mA}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.2	V	$I_c=10\text{ mA}$ $I_b=1\text{ mA}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.3	V	$I_c=50\text{ mA}$ $I_b=5\text{ mA}$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			0.85	V	$I_c=10\text{ mA}$ $I_b=1\text{ mA}$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			0.95	V	$I_c=50\text{ mA}$ $I_b=5\text{ mA}$
Output Capacitance	C_{ob}			4	pF	$V_{cb}=5V$ $I_e=0$ $f=1\text{ MHz}$
Current Gain-Bandwidth Product	f_T	300			MHz	$V_{ce}=20V$ $I_c=10\text{ mA}$ $f=100\text{ MHz}$